



SHENZHEN TUOFENG SEMICONDUCTOR TECHNOLOGY CO.,LTD

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

SGT MOS、低内阻、低结电容开关损耗小

TFS050N03MG**Description**

The TFS050N03MG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other switching application.

General Feature $V_{DS} = 30V$, $I_D = 40A$ $R_{DS(ON)\text{ Typ}} = 4.9m\Omega$ @ $V_{GS}=10V$ $R_{DS(ON)\text{ Typ}} = 6.9m\Omega$ @ $V_{GS}=4.5V$

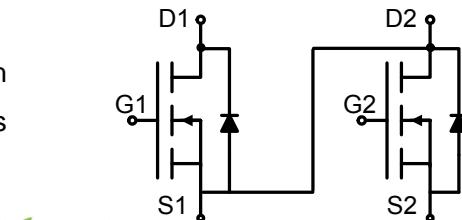
High Power and current handing capability Lead free product is acquired

Surface mount package

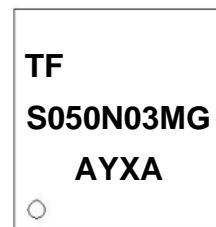
Application

Battery switch

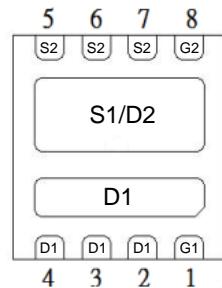
DC/DC converter



Schematic diagram



Pin 1



DFN3030-8L

•Package Marking and Ordering Information:

Part NO.	TFS050N03MG		
Marking1	S050N03MG: TFS050N03MG		
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;		
Basic ordering unit (pcs)	5000		

•Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@TC=25^\circ C$	40	A
	$I_D@TC=75^\circ C$	30	A
	$I_D@TC=100^\circ C$	25	A
Pulsed Drain Current ^①	I_{DM}	115	A
Total Power Dissipation	$P_D@TC=25^\circ C$	30	W
Total Power Dissipation	$P_D@TA=25^\circ C$	1.0	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E_{AS}	40	mJ



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● Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	4.6	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	57	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

● Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	30	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30 V _{GS} = 0V	-	-	1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V ,V _{DS} = 0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	4.9	6.5	mΩ
		V _{GS} =4.5V, I _D =8.0A	-	6.9	9.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 25V, I _D =10A	-	15	-	S
Source-drain voltage	V _{SD}	I _S =10A	-	0.82	1.20	V

● Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =15V V _{GS} = 0V	-	750	-	pF
Output capacitance	C _{oss}		-	333	-	
Reverse transfer capacitance	C _{rss}		-	32.0	-	

● Switching Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Turn-on delay time	t _{d(on)}	V _{DD} = 15V I _D = 10A R _G = 3.0 V _{GS} = 10V	-	4.3	-	nS
Rise time	t _r		-	23.0	-	
Turn-off delay time	t _{d(off)}		-	12.5	-	
Fall time	t _f		-	6.0	-	
Total gate charge	Q _g	V _{DD} = 15V I _D = 10A V _{GS} = 10V	-	13.8	-	nC
Gate - Source charge	Q _{gs}		-	2.22	-	
Gate - Drain charge	Q _{gd}		-	3.23	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;



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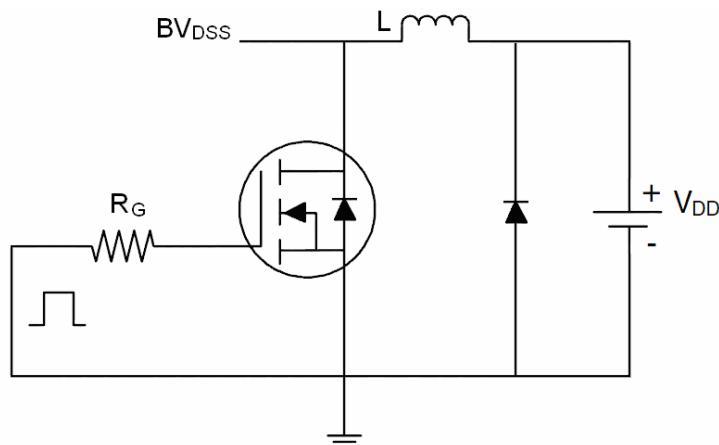
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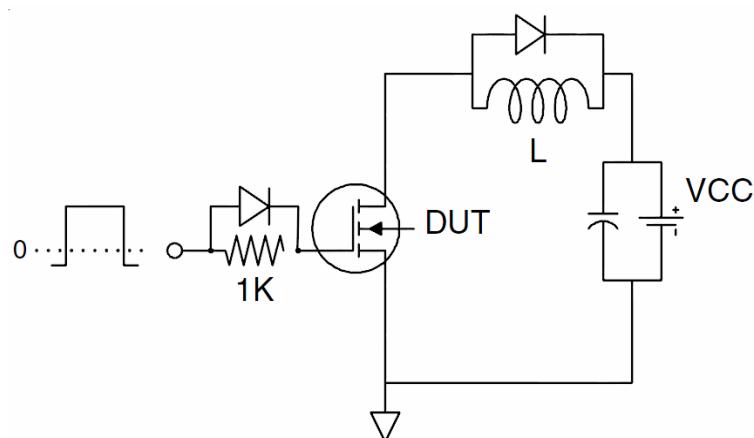
TFS050N03MG

Test Circuit

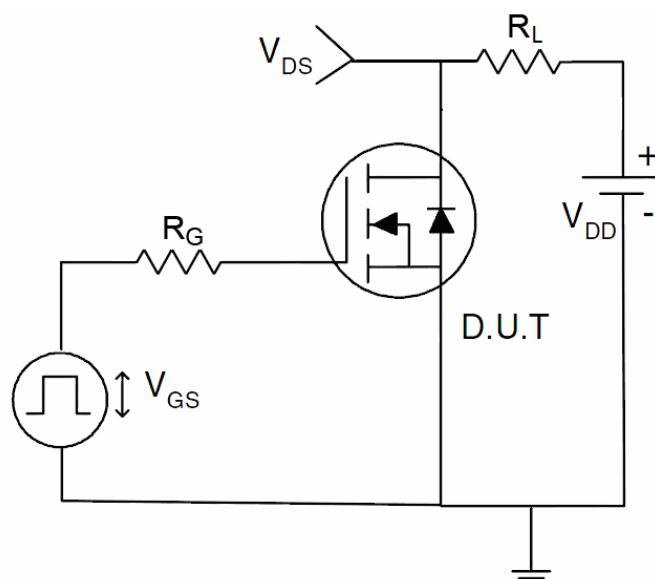
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

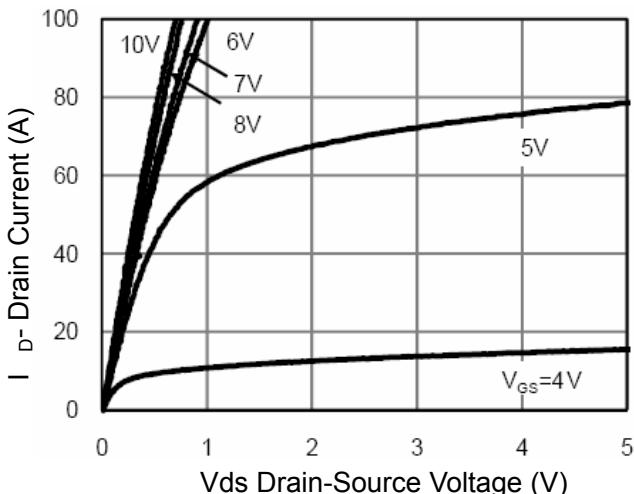


Figure 1 Output Characteristics

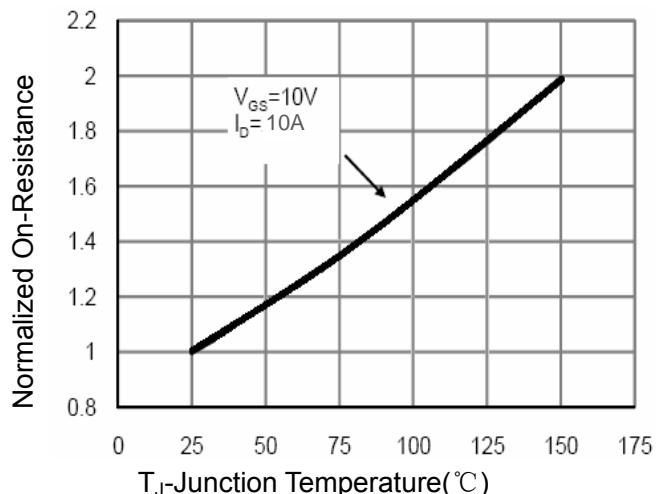


Figure 4 Rdson-JunctionTemperature

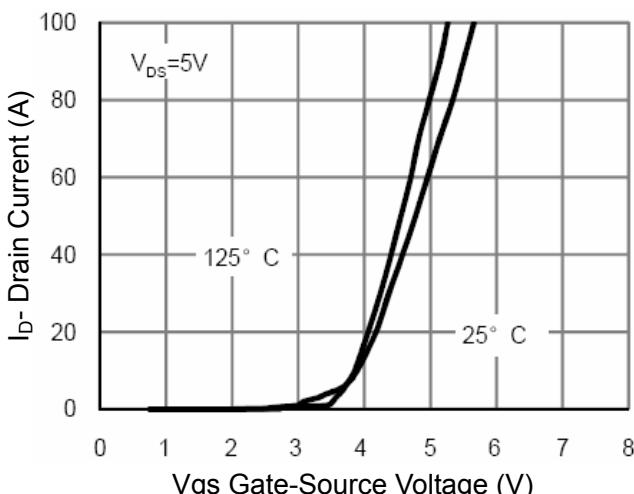


Figure 2 Transfer Characteristics

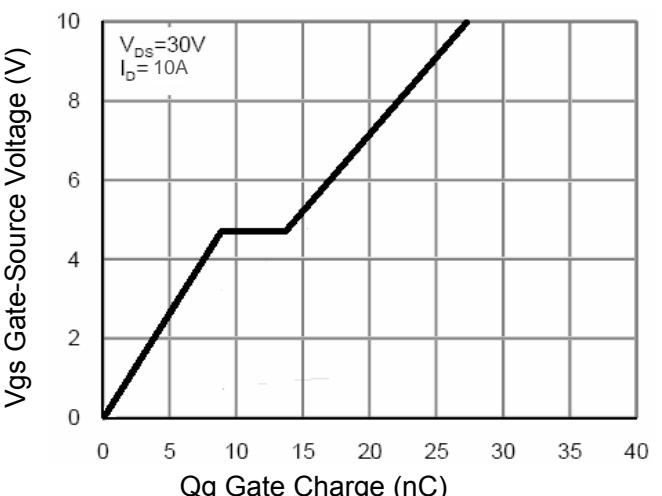


Figure 5 Gate Charge

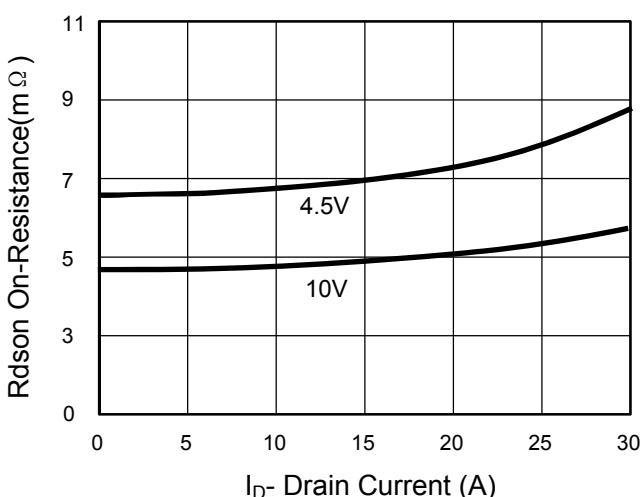


Figure 3 Rdson- Drain Current

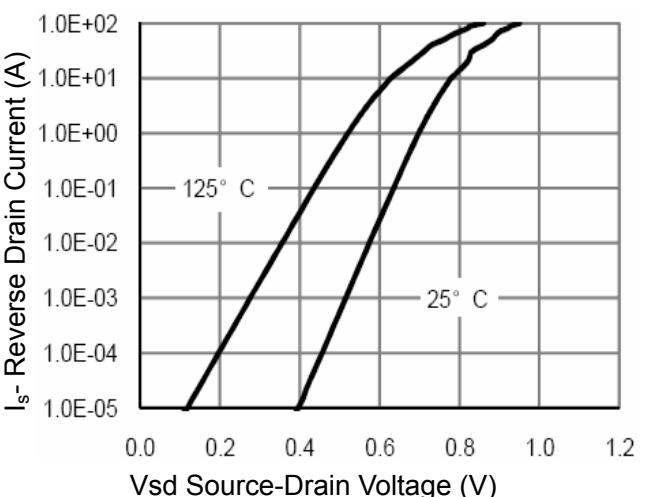


Figure 6 Source- Drain Diode Forward

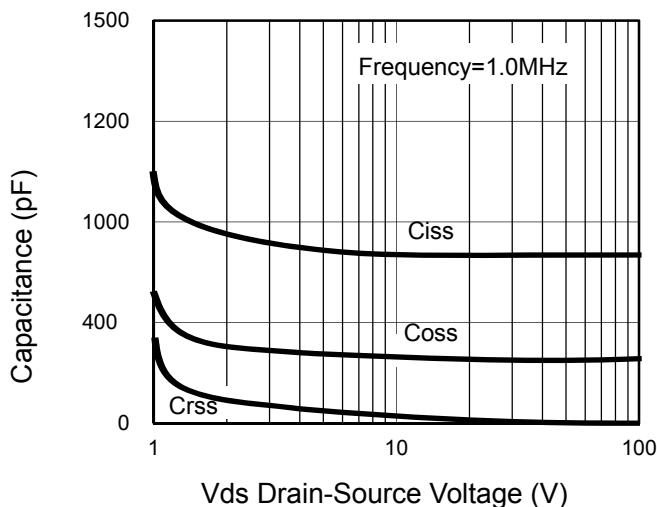


Figure 7 Capacitance vs Vds

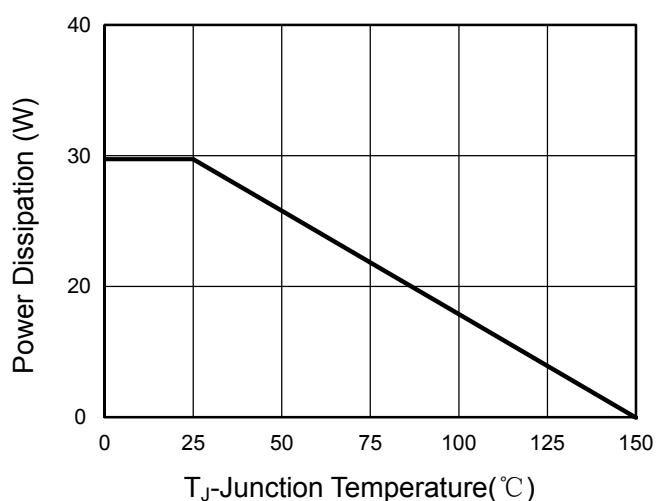


Figure 9 Power De-rating

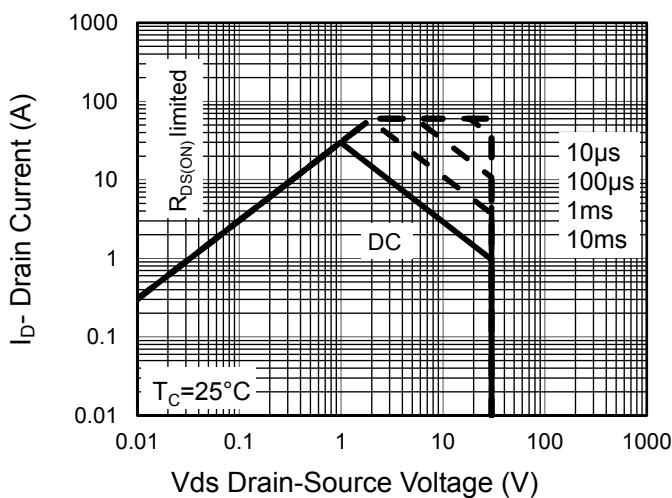


Figure 8 Safe Operation Area

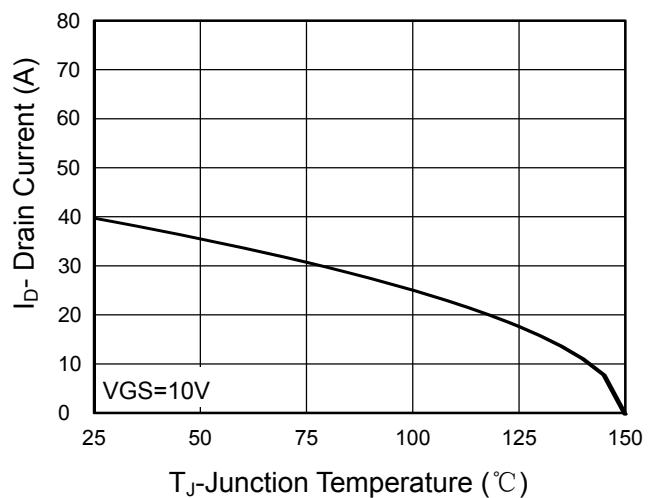


Figure 10 Current De-rating

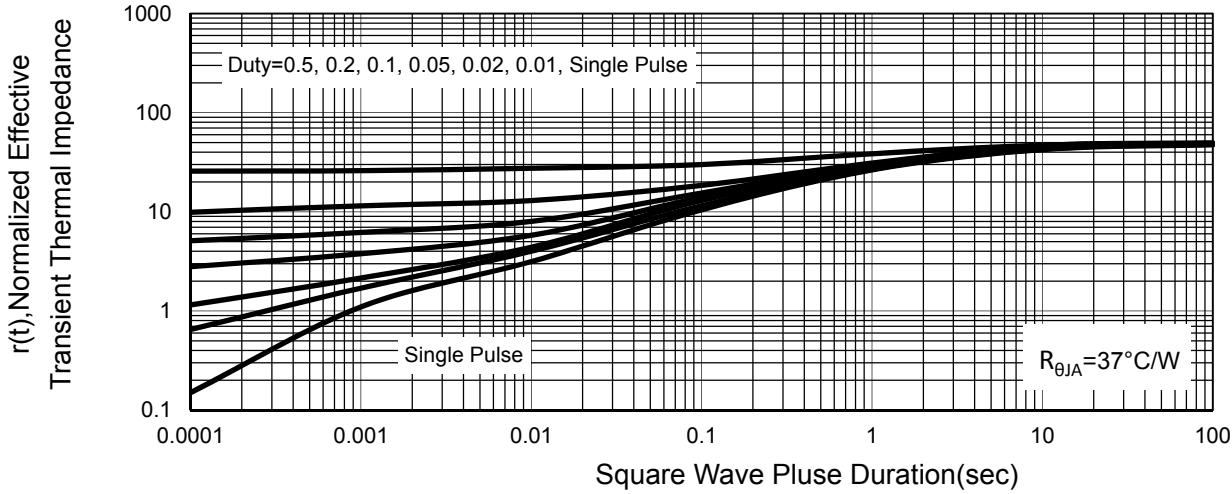


Figure 11 Normalized Maximum Transient Thermal Impedance



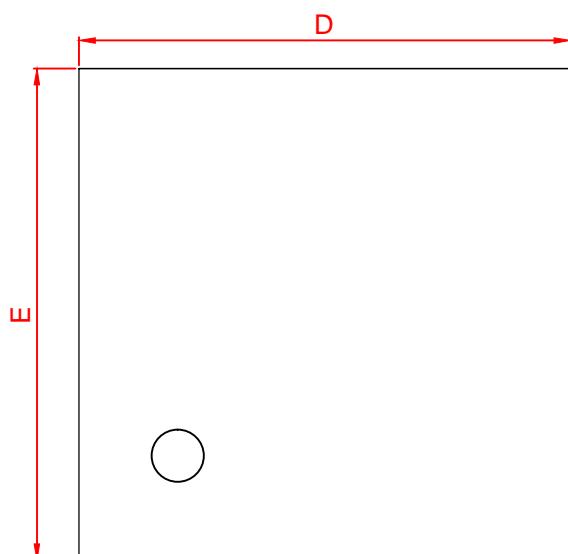
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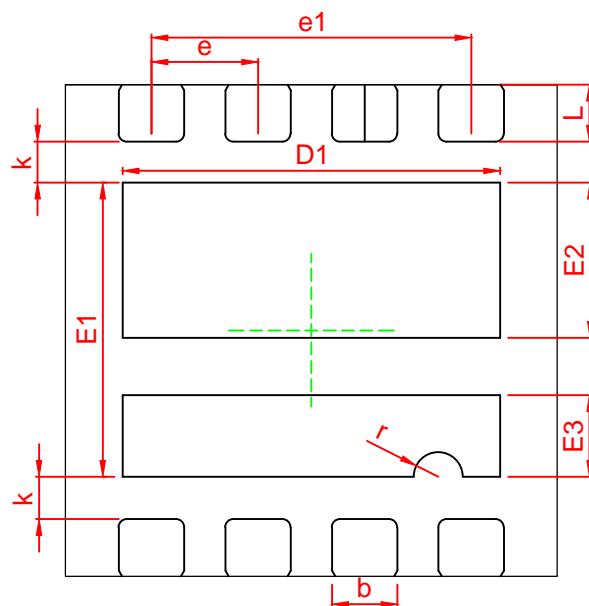
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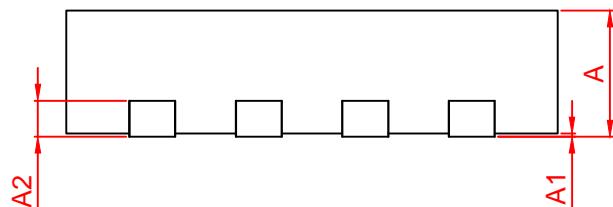
DFN3030-8L



TOPVIEW



BOTTOMVIEW



SIDEVIEW

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
* A1	0.00	0.02	0.05
* b	0.35	0.40	0.45
* A2	0.203 BSC		
* D	2.95	3.00	3.05
* E	2.95	3.00	3.05
* D1	2.25	2.30	2.35
* E1	1.70	1.80	1.90
* E2	0.90	0.95	1.00
* E3	0.45	0.50	0.55
* e	0.65 BSC		
* e1	1.95 BSC		
* k	0.20	0.25	0.30
* L	0.30	0.35	0.40
r	0.15 REF		